



# ATP602 — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- ON-resistance  $R_{DS(on)}=2.1\Omega$  (typ.)
- 10V drive
- Input capacitance  $C_{iss}=350pF$  (typ.)
- Halogen free compliance

### Specifications

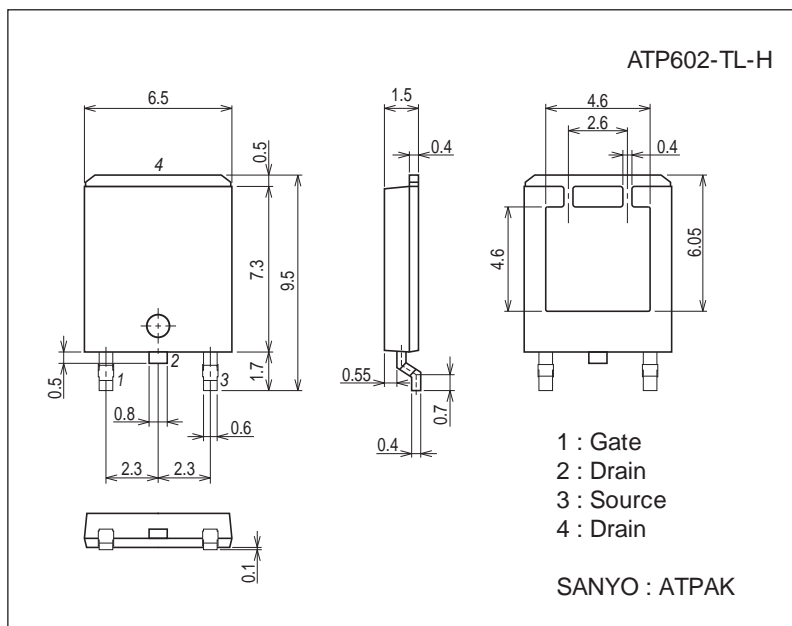
Absolute Maximum Ratings at  $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		600	V
Gate-to-Source Voltage	$V_{GSS}$		$\pm 30$	V
Drain Current (DC)	$I_D$		5	A
Drain Current (Pulse)	$I_{DP}$	$PW \leq 10\mu s$ , duty cycle $\leq 1\%$	15	A
Allowable Power Dissipation	$P_D$	$T_c=25^\circ C$	70	W
Channel Temperature	$T_{ch}$		150	$^\circ C$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ C$
Avalanche Energy (Single Pulse) *1	$E_{AS}$		74	mJ
Avalanche Current *2	$I_{AV}$		5	A

Note : \*1  $V_{DD}=99V$ ,  $L=5mH$ ,  $I_{AV}=5A$  (Fig.1)  
 \*2  $L \leq 5mH$ , Single pulse

### Package Dimensions

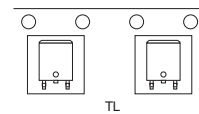
unit : mm (typ)  
 7057-001



### Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

### Packing Type: TL



### Marking



### Electrical Connection

